512K x 8 LOW VOLTAGE, ULTRA LOW POWER CMOS STATIC RAM

FEBRUARY 2012

FEATURES

- High-speed access time: 35, 45, 55 ns
- CMOS low power operation

  36 mW (typical) operating

  9 µW (typical) CMOS standby
- TTL compatible interface levels
- Single power supply

  1.65V – 2.2V V_{DD} (IS62WV5128DALL)

  2.3V – 3.6V V_{DD} (IS62WV5128DBLL)
- Fully static operation: no clock or refresh required
- Three state outputs
- Industrial and Automotive temperature support
- Lead-free available

DESCRIPTION

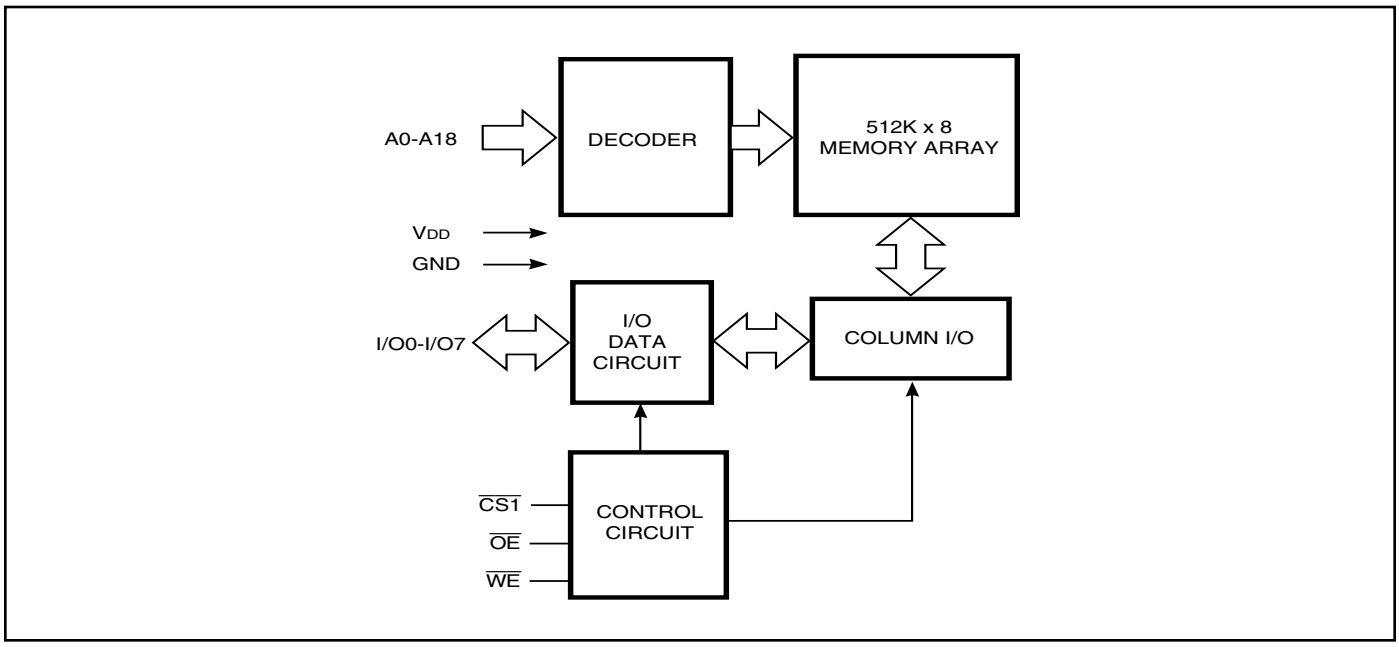
The *ISSI* IS62WV5128DALL / IS62WV5128DBLL are high-speed, 4M bit static RAMs organized as 512K words by 8 bits. It is fabricated using *ISSI*'s high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields high-performance and low power consumption devices.

When $\overline{CS1}$ is HIGH (deselected) the device assumes a standby mode at which the power dissipation can be reduced down with CMOS input levels.

Easy memory expansion is provided by using Chip Enable and Output Enable inputs. The active LOW Write Enable ($\overline{WE}$) controls both writing and reading of the memory.

The IS62WV5128DALL and IS62WV5128DBLL are packaged in the JEDEC standard 32-pin TSOP (TYPE I), 32-pin sTSOP (TYPE I), 32-pin TSOP (Type II), 32-pin SOP and 36-pin mini BGA.

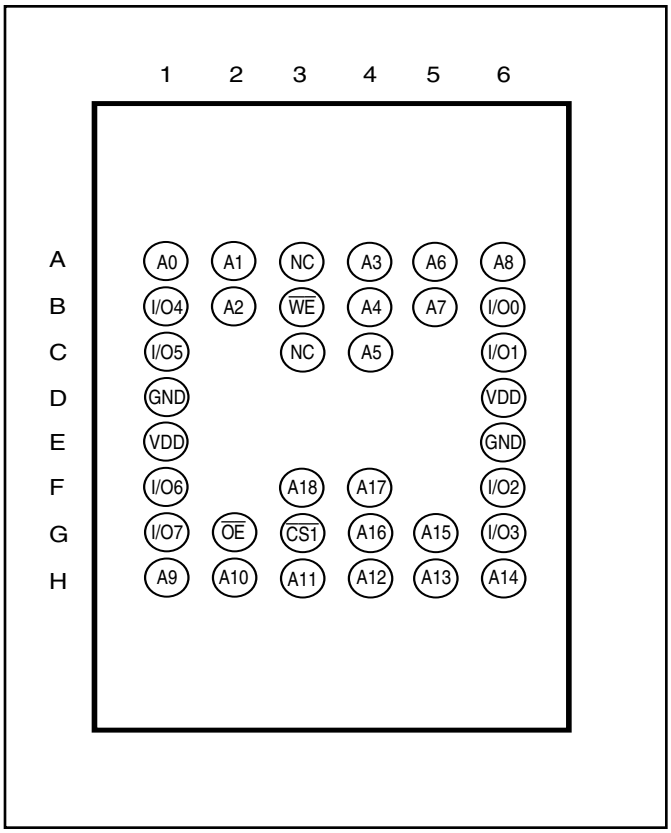
FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTIONS

A0-A18	Address Inputs
$\overline{CS1}$	Chip Enable 1 Input
$\overline{OE}$	Output Enable Input
$\overline{WE}$	Write Enable Input
I/O0-I/O7	Input/Output
NC	No Connection
V_{DD}	Power
GND	Ground

36-pin mini BGA (B) (6mm x 8mm) (Package Code B)

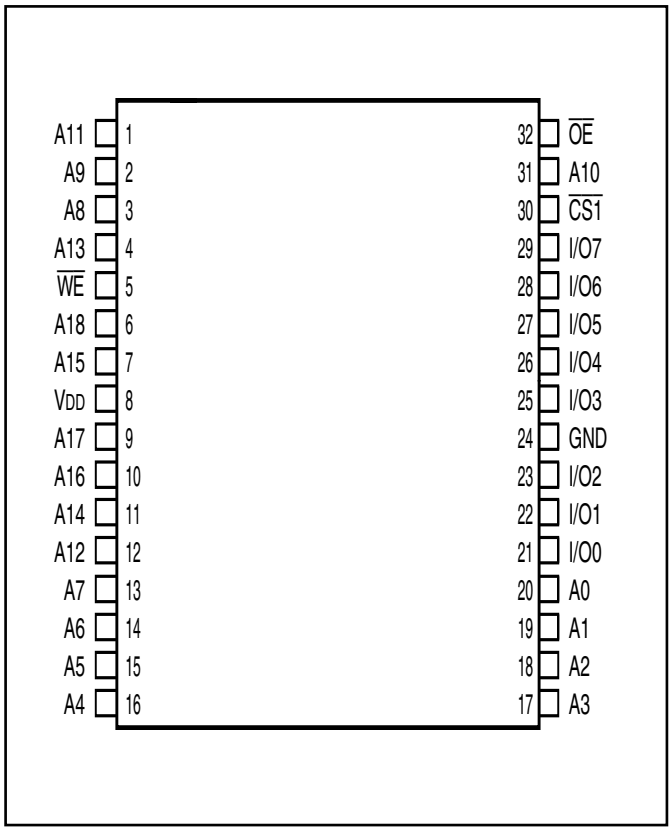


PIN DESCRIPTIONS

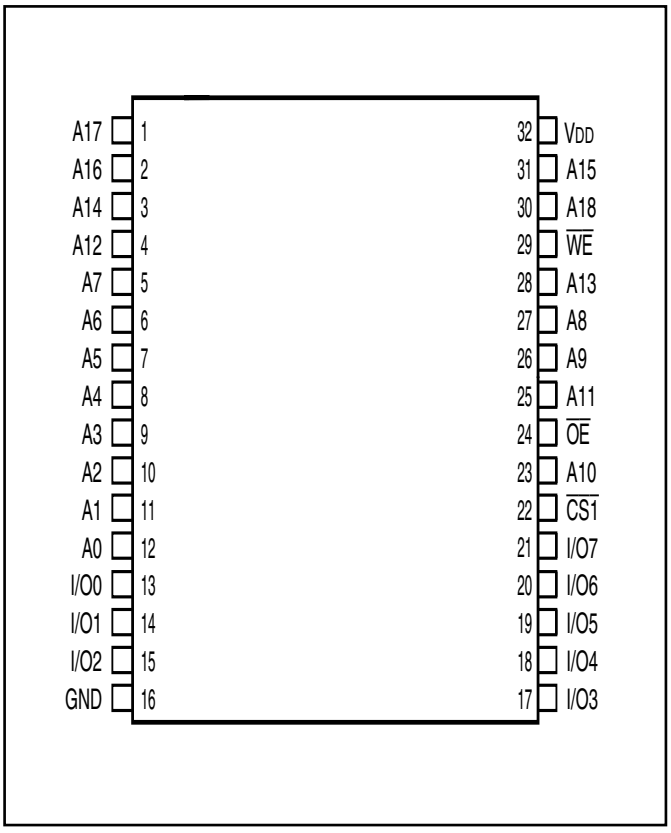
A0-A18	Address Inputs
$\overline{CS1}$	Chip Enable 1 Input
$\overline{OE}$	Output Enable Input
$\overline{WE}$	Write Enable Input
I/O0-I/O7	Input/Output
V_{DD}	Power
GND	Ground

PIN CONFIGURATION

32-pin TSOP (TYPE I), (Package Code T)
32-pin sTSOP (TYPE I) (Package Code H)



32-pin SOP (Package Code Q)
32-pin TSOP (TYPE II) (Package Code T2)



TRUTH TABLE

Mode	$\overline{WE}$	$\overline{CS1}$	$\overline{OE}$	I/O Operation	V_{DD} Current
Not Selected (Power-down)	X	H	X	High-Z	I_{SB1}, I_{SB2}
Output Disabled	H	L	H	High-Z	I_{CC}
Read	H	L	L	D_{OUT}	I_{CC}
Write	L	L	X	D_{IN}	I_{CC}

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit
V_{TERM}	Terminal Voltage with Respect to GND	–0.5 to V_{DD} + 0.5	V
V_{DD}	V_{DD} Relates to GND	–0.3 to 4.0	V
T_{STG}	Storage Temperature	–65 to +150	°C
P_T	Power Dissipation	1.0	W

Notes:
1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

CAPACITANCE(1,2)

Symbol	Parameter	Conditions	Max.	Unit
C_{IN}	Input Capacitance	V_{IN} = 0V	6	pF
$C_{I/O}$	Input/Output Capacitance	V_{OUT} = 0V	8	pF

Notes:
1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T_A = 25°C, f = 1 MHz, V_{DD} = 3.3V.

AC TEST CONDITIONS

Parameter	Unit (2.3V-3.6V)	Unit (3.3V ± 5%)	Unit (1.65V-2.2V)
Input Pulse Level	0.4V to V_{DD} - 0.3V	0.4V to V_{DD} - 0.3V	0.4V to V_{DD} - 0.3V
Input Rise and Fall Times	1V/ ns	1V/ ns	1V/ ns
Input and Output Timing and Reference Level (V_{Ref})	VDD /2	$\frac{VDD}{2}$ + 0.05	0.9V
Output Load	See Figures 1 and 2	See Figures 1 and 2	See Figures 1 and 2
R1 (Ω)	1005	1213	13500
R2 (Ω)	820	1378	10800
V_{TM} (V)	3.0V	3.3V	1.8V

AC TEST LOADS

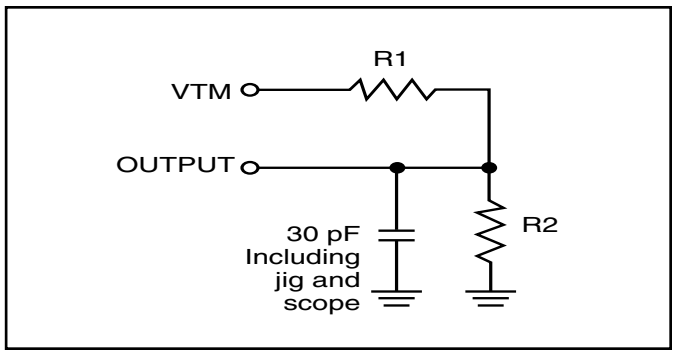


Figure 1.

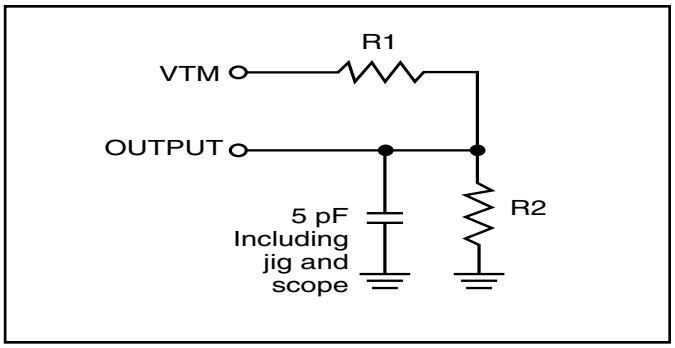


Figure 2.

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

V_{DD} = 3.3V ± 5%

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	V_{DD} = Min., I_{OH} = –1 mA	2.4	—	V
V_{OL}	Output LOW Voltage	V_{DD} = Min., I_{OL} = 2.1 mA	—	0.4	V
V_{IH}	Input HIGH Voltage		2	V_{DD} + 0.3	V
V_{IL}	Input LOW Voltage[1]		–0.3	0.8	V
I_{LI}	Input Leakage	GND ≤ V_{IN} ≤ V_{DD}	–1	1	µA
I_{LO}	Output Leakage	GND ≤ V_{OUT} ≤ V_{DD}, Outputs Disabled	–1	1	µA

Note:
1. V_{IL} (min.) = –0.3V DC; V_{IL} (min.) = –2.0V AC (pulse width < 10 ns). Not 100% tested.
   V_{IH} (max.) = V_{DD} + 0.3V DC; V_{IH} (max.) = V_{DD} + 2.0V AC (pulse width < 10 ns). Not 100% tested.

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

V_{DD} = 2.3V-3.6V

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	V_{DD} = Min., I_{OH} = –1.0 mA	1.8	—	V
V_{OL}	Output LOW Voltage	V_{DD} = Min., I_{OL} = 2.1 mA	—	0.4	V
V_{IH}	Input HIGH Voltage		2.0	V_{DD} + 0.3	V
V_{IL}	Input LOW Voltage[1]		–0.3	0.8	V
I_{LI}	Input Leakage	GND ≤ V_{IN} ≤ V_{DD}	–1	1	µA
I_{LO}	Output Leakage	GND ≤ V_{OUT} ≤ V_{DD}, Outputs Disabled	–1	1	µA

Note:
1. V_{IL} (min.) = –0.3V DC; V_{IL} (min.) = –2.0V AC (pulse width < 10 ns). Not 100% tested.
   V_{IH} (max.) = V_{DD} + 0.3V DC; V_{IH} (max.) = V_{DD} + 2.0V AC (pulse width < 10 ns). Not 100% tested.

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

V_{DD} = 1.65V-2.2V

Symbol	Parameter	Test Conditions	V_{DD}	Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = -0.1 mA	1.65-2.2V	1.4	—	V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA	1.65-2.2V	—	0.2	V
V_{IH}	Input HIGH Voltage		1.65-2.2V	1.4	V_{DD} + 0.2	V
V_{IL}[1]	Input LOW Voltage		1.65-2.2V	–0.2	0.4	V
I_{LI}	Input Leakage	GND ≤ V_{IN} ≤ V_{DD}		–1	1	µA
I_{LO}	Output Leakage	GND ≤ V_{OUT} ≤ V_{DD}, Outputs Disabled		–1	1	µA

Note:
1. V_{IL} (min.) = –0.3V DC; V_{IL} (min.) = –2.0V AC (pulse width < 10 ns). Not 100% tested.
   V_{IH} (max.) = V_{DD} + 0.3V DC; V_{IH} (max.) = V_{DD} + 2.0V AC (pulse width < 10 ns). Not 100% tested.

OPERATING RANGE (V_{DD})

Range	Ambient Temperature	V_{DD}	Speed
Commercial	0°C to +70°C	1.65V-2.2V	45ns
Industrial	–40°C to +85°C	1.65V-2.2V	55ns
Automotive	–40°C to +125°C	1.65V-2.2V	55ns

OPERATING RANGE (V_{DD})

Range	Ambient Temperature	V_{DD} (45 ns)	V_{DD} (35 ns)
Commercial	0°C to +70°C	2.3V-3.6V	3.3V±5%
Industrial	–40°C to +85°C	2.3V-3.6V	3.3V±5%

OPERATING RANGE (V_{DD})

Range	Ambient Temperature	V_{DD} (45 ns)
Automotive	–40°C to +125°C	2.3V-3.6V

POWER SUPPLY CHARACTERISTICS[1] (Over Operating Range)

Symbol	Parameter	Test Conditions		-35 Min.	-35 Max.	-45 Min.	-45 Max.	-55 Min.	-55 Max.	Unit
I_{CC}	V_{DD} Dynamic Operating Supply Current	V_{DD} = Max., I_{OUT} = 0 mA, f = f_{MAX} $\overline{CE}$ = V_{IL} $V_{IN} \geq V_{DD} - 0.3V$, or $V_{IN} \leq$ 0.4V	Com.	—	20	—	15	—	15	mA
			Ind.	—	25	—	20	—	20	
			Auto.	—	30	—	25	—	25	
			typ.[2]	10						
I_{CC1}	Operating Supply Current	V_{DD} = Max., I_{OUT} = 0 mA, f = 0 $\overline{CE}$ = V_{IL} $V_{IN} \geq V_{DD} - 0.3V$, or $V_{IN} \leq$ 0.4V	Com.	—	3	—	3	—	3	mA
			Ind.	—	3	—	3	—	3	
			Auto.	—	3	—	3	—	3	
I_{SB2}	CMOS Standby Current (CMOS Inputs)	V_{DD} = Max., $\overline{CE} \geq V_{DD} - 0.2V$, $V_{IN} \geq V_{DD} - 0.2V$, or $V_{IN} \leq$ 0.2V, f = 0	Com.	—	5	—	5	—	5	µA
			Ind.	—	10	—	10	—	10	
			Auto.	—	30	—	30	—	30	
			typ.[2]	2						

Note:

1. At f = f_{MAX}, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.
2. Typical values are measured at V_{DD} = 3.0V, T_A = 25°C and not 100% tested.

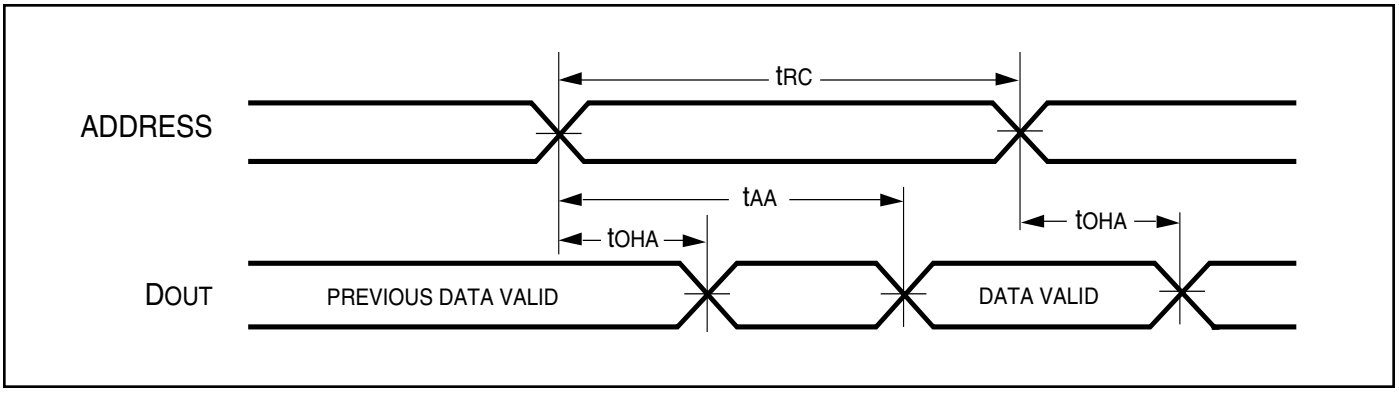
READ CYCLE SWITCHING CHARACTERISTICS[1] (Over Operating Range)

Symbol	Parameter	35 ns Min.	35 ns Max.	45 ns Min.	45 ns Max.	55 ns Min.	55 ns Max.	Unit
t_{RC}	Read Cycle Time	35	—	45	—	55	—	ns
t_{AA}	Address Access Time	—	35	—	45	—	55	ns
t_{OHA}	Output Hold Time	10	—	10	—	10	—	ns
t_{ACS1}	$\overline{CS1}$ Access Time	—	35	—	45	—	55	ns
t_{DOE}	$\overline{OE}$ Access Time	—	10	—	20	—	25	ns
t_{HZOE}[2]	$\overline{OE}$ to High-Z Output	—	10	—	15	—	20	ns
t_{LZOE}[2]	$\overline{OE}$ to Low-Z Output	3	—	5	—	5	—	ns
t_{HZCS1}	$\overline{CS1}$ to High-Z Output	0	10	0	15	0	20	ns
t_{LZCS1}	$\overline{CS1}$ to Low-Z Output	5	—	10	—	10	—	ns

Notes:
1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4 to V_{DD}-0.2V/V_{DD}-0.3V and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

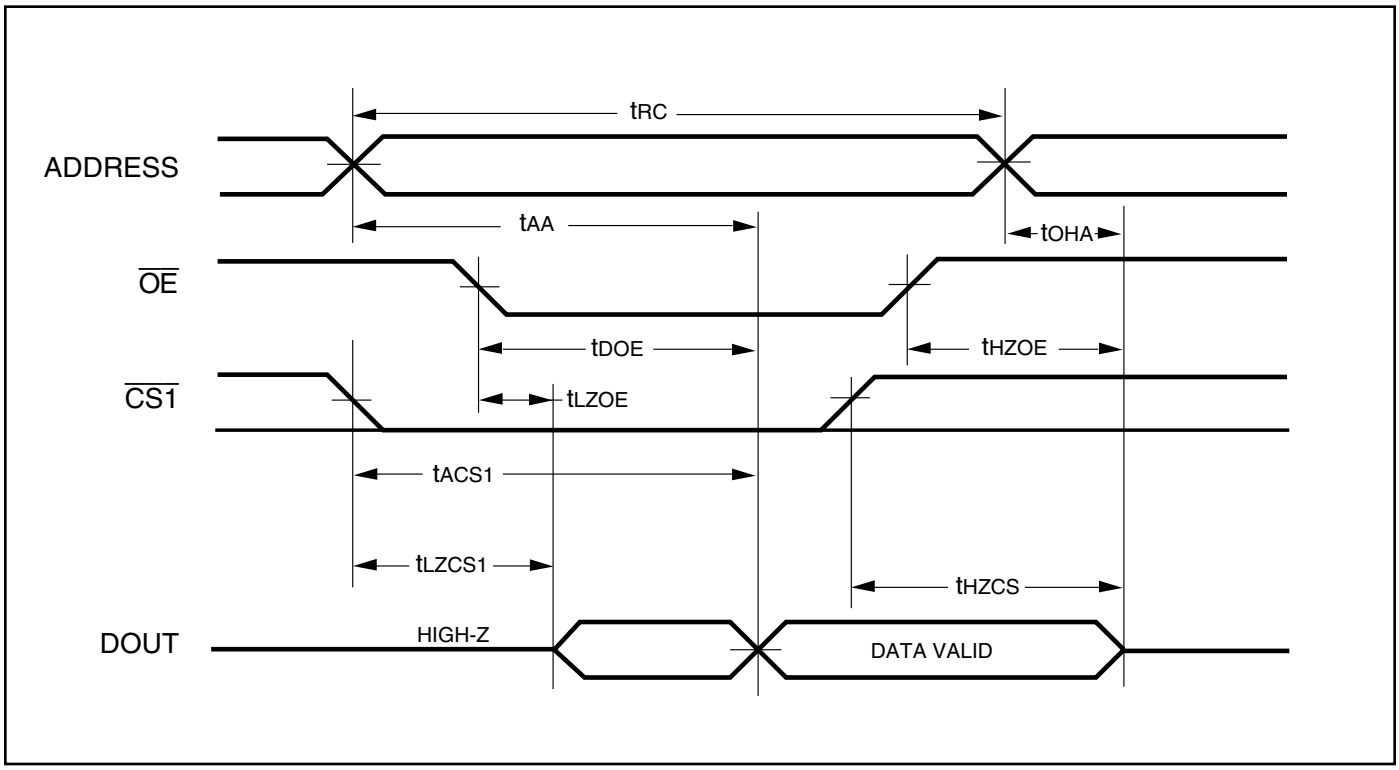
AC WAVEFORMS

READ CYCLE NO. 1[1,2] (Address Controlled) ($\overline{CS1}$ = $\overline{OE}$ = V_{IL}, $\overline{WE}$ = V_{IH})



AC WAVEFORMS

READ CYCLE NO. 2[1,3] ($\overline{CS1}$, $\overline{OE}$ Controlled)



Notes:
1. $\overline{WE}$ is HIGH for a Read Cycle.
2. The device is continuously selected. $\overline{OE}$, $\overline{CS1}$= V_{IL}. $\overline{WE}$=V_{IH}.
3. Address is valid prior to or coincident with $\overline{CS1}$ LOW transition.

WRITE CYCLE SWITCHING CHARACTERISTICS[1,2] (Over Operating Range)

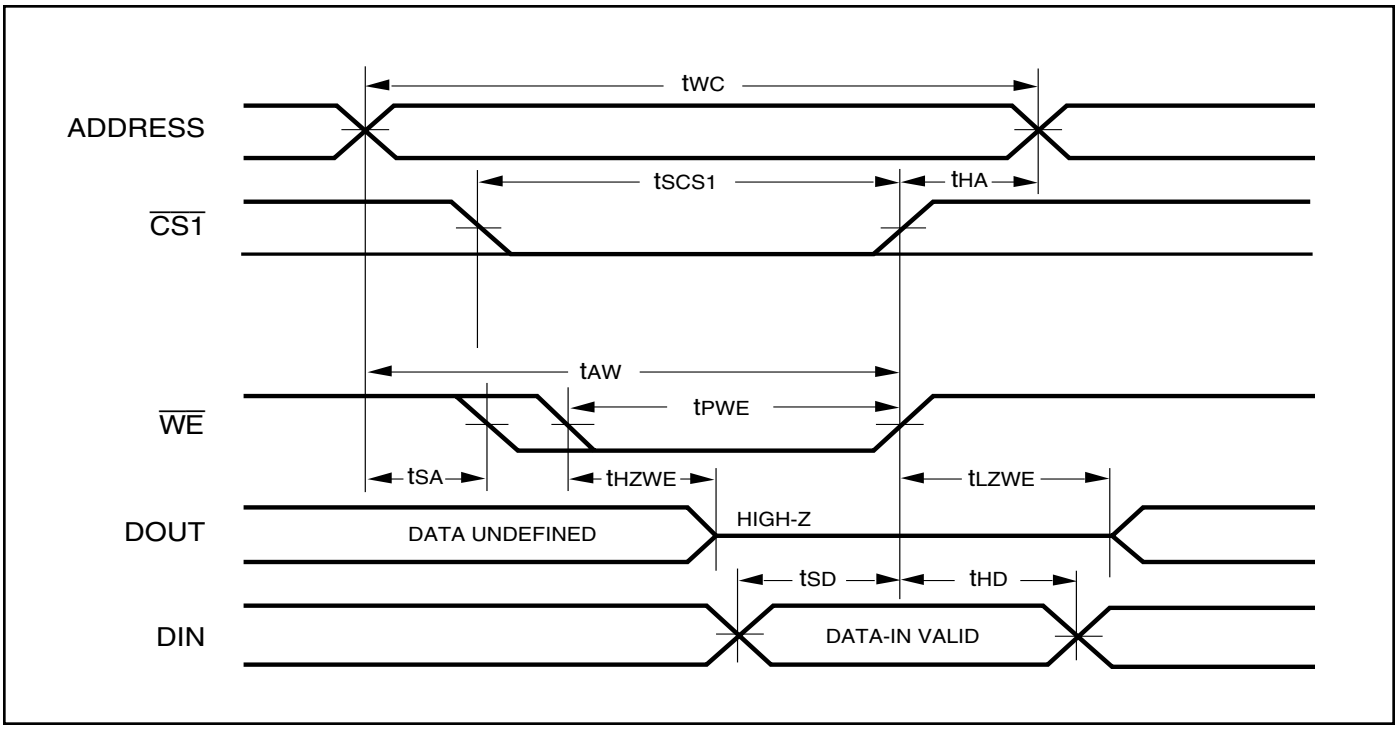
Symbol	Parameter	35ns Min.	35ns Max.	45ns Min.	45ns Max.	55 ns Min.	55 ns Max.	Unit
t_{WC}	Write Cycle Time	35	—	45	—	55	—	ns
t_{SCS1}	$\overline{CS1}$ to Write End	25	—	35	—	45	—	ns
t_{AW}	Address Setup Time to Write End	25	—	35	—	45	—	ns
t_{HA}	Address Hold from Write End	0	—	0	—	0	—	ns
t_{SA}	Address Setup Time	0	—	0	—	0	—	ns
t_{PWE}	$\overline{WE}$ Pulse Width	25	—	35	—	40	—	ns
t_{SD}	Data Setup to Write End	20	—	20	—	25	—	ns
t_{HD}	Data Hold from Write End	0	—	0	—	0	—	ns
t_{HZWE}[3]	$\overline{WE}$ LOW to High-Z Output	—	10	—	20	—	20	ns
t_{LZWE}[3]	$\overline{WE}$ HIGH to Low-Z Output	3	—	5	—	5	—	ns

Notes:

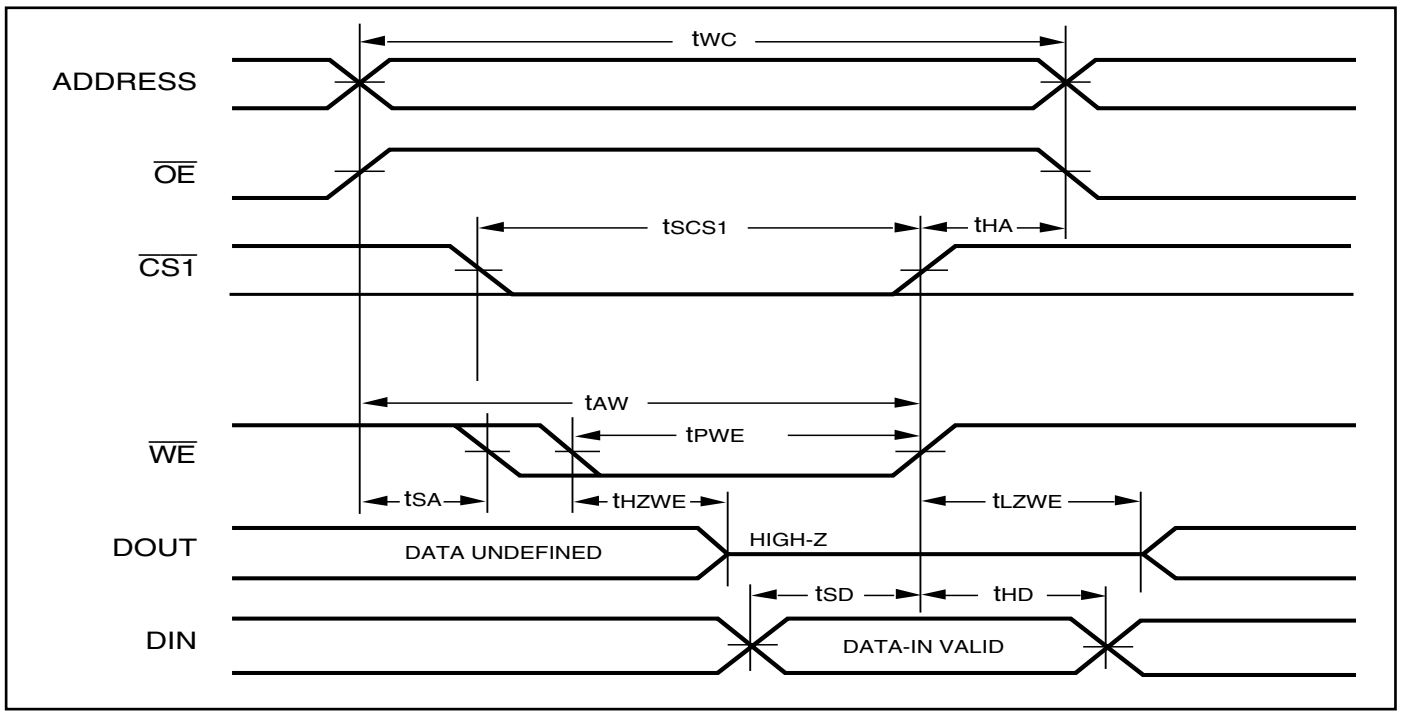
1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 0.9V/1.5V, input pulse levels of 0.4V to V_{DD}-0.2V/V_{DD}-0.3V and output loading specified in Figure 1.
2. The internal write time is defined by the overlap of $\overline{CS1}$ LOW and $\overline{WE}$ LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
3. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

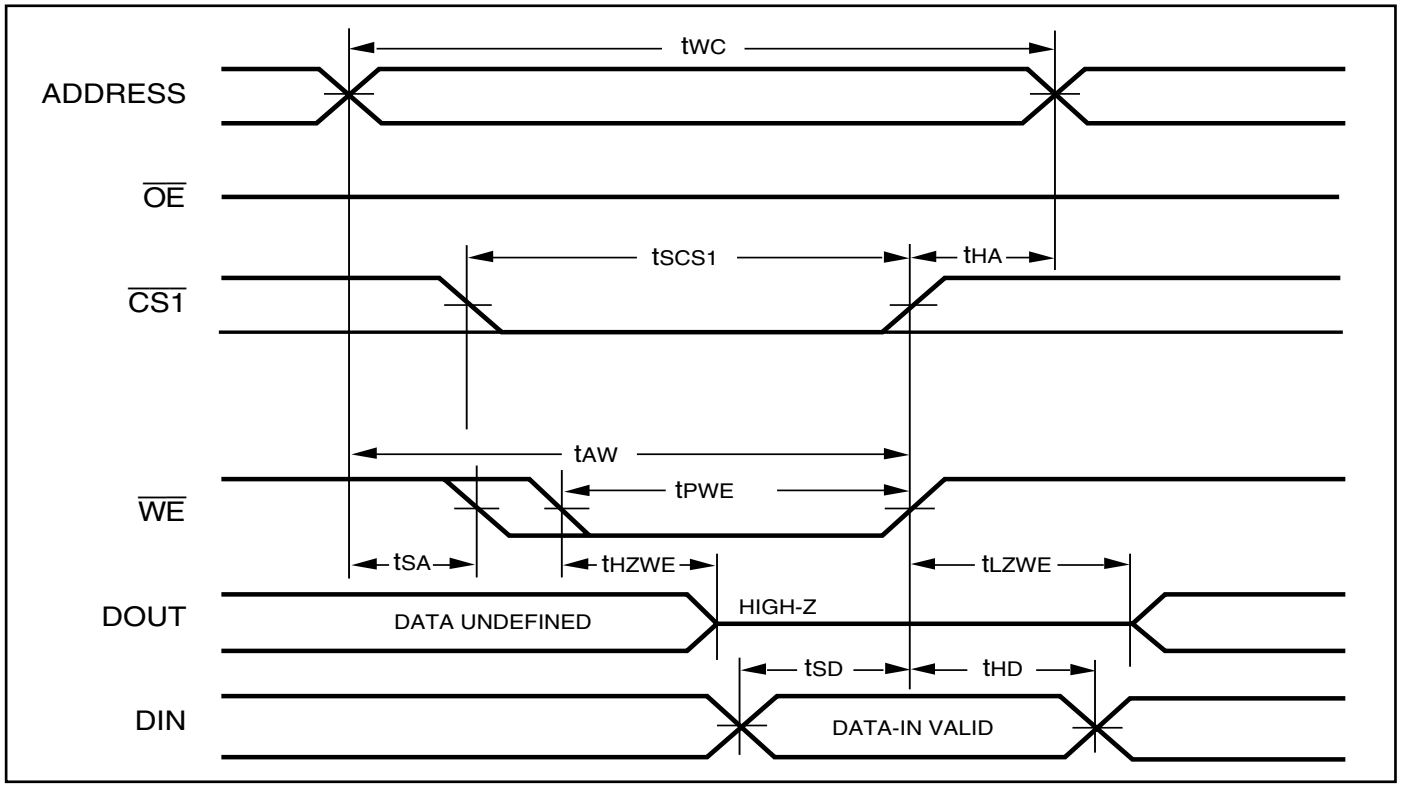
WRITE CYCLE NO. 1 ($\overline{CS1}$ Controlled, $\overline{OE}$ = HIGH or LOW)



WRITE CYCLE NO. 2 ($\overline{WE}$ Controlled: $\overline{OE}$ is HIGH During Write Cycle)



WRITE CYCLE NO. 3 ($\overline{WE}$ Controlled: $\overline{OE}$ is LOW During Write Cycle)

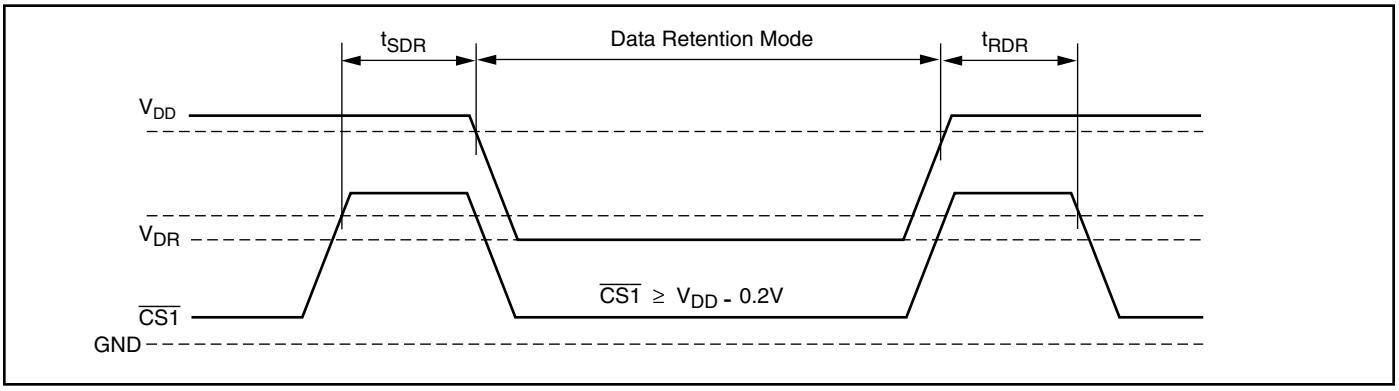


DATA RETENTION SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Min.	Max.	Unit
V_{DR}	V_{DD} for Data Retention	See Data Retention Waveform		1.2	3.6	V
I_{DR}	Data Retention Current	V_{DD} = 1.2V, $\overline{CS1} \geq V_{DD} - 0.2V$	Com.	—	3	µA
			Ind.	—	7	
			Auto.	—	20	
			typ.(1)	1		
t_{SDR}	Data Retention Setup Time	See Data Retention Waveform		0	—	ns
t_{RDR}	Recovery Time	See Data Retention Waveform		t_{RC}	—	ns

Note: 1. Typical values are measured at V_{DD} = 3.0V, T_A = 25°C and not 100% tested.

DATA RETENTION WAVEFORM ($\overline{CS1}$ Controlled)



ORDERING INFORMATION

IS62WV5128DALL (1.65V-2.2V)

Industrial Range: –40°C to +85°C

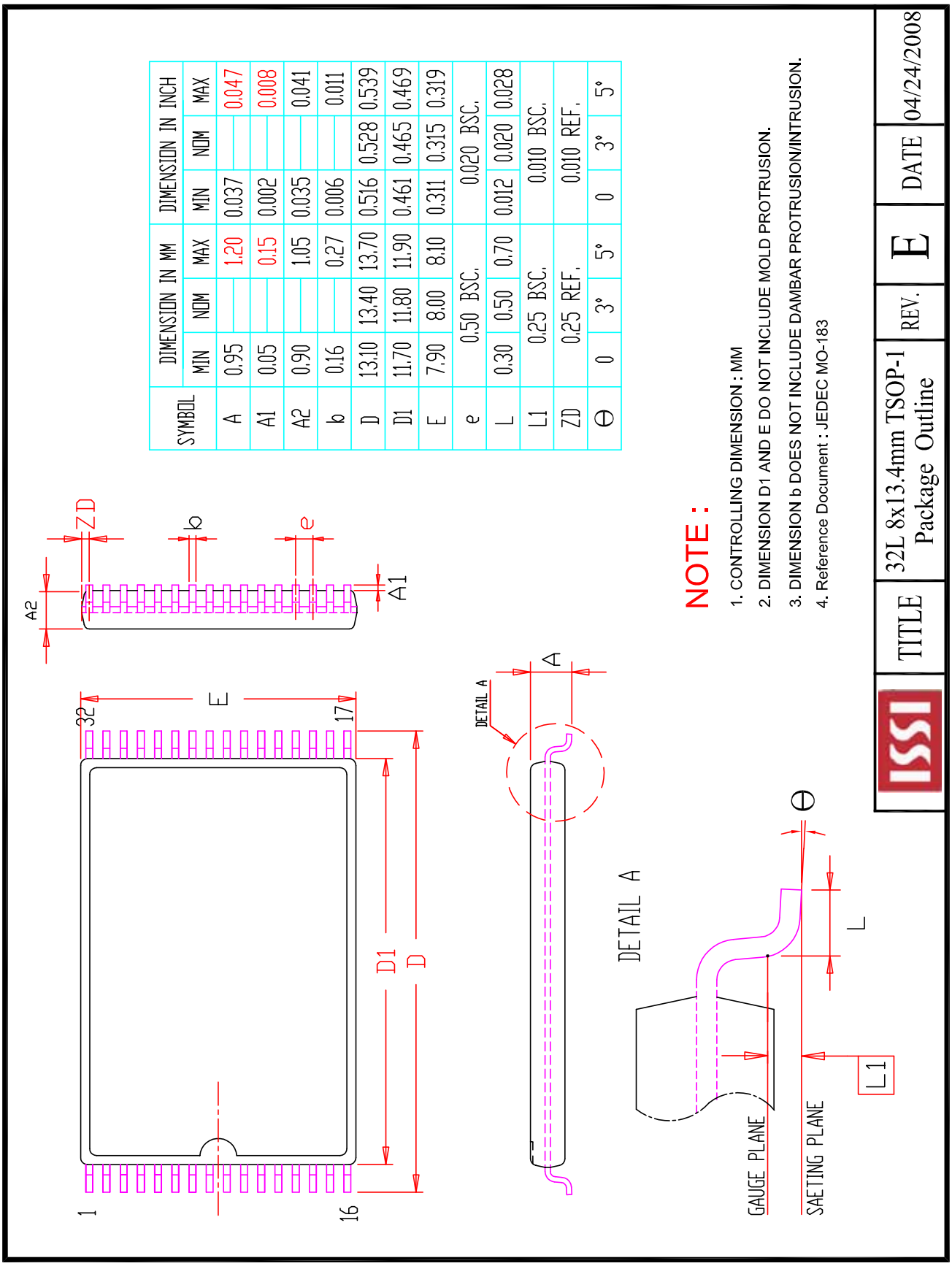
Speed (ns)	Order Part No.	Package
55	IS62WV5128DALL-55TI	TSOP, TYPE I (8 x 20 mm)
	IS62WV5128DALL-55TLI	TSOP, TYPE I, Lead-free (8 x 20 mm)
55	IS62WV5128DALL-55T2I	TSOP, TYPE II
	IS62WV5128DALL-55T2LI	TSOP, TYPE II, Lead-free
55	IS62WV5128DALL-55HI	sTSOP, TYPE I (8 x 13.4 mm)
	IS62WV5128DALL-55HLI	sTSOP, TYPE I, Lead-free (8 x 13.4 mm)
55	IS62WV5128DALL-55BI	mini BGA (6mmx8mm)
	IS62WV5128DALL-55BLI	mini BGA (6mmx8mm), Lead-free

ORDERING INFORMATION

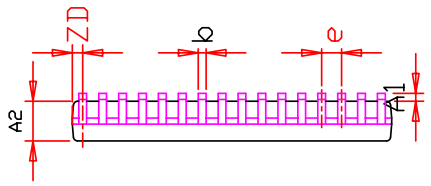
IS62WV5128BLL (2.3V - 3.6V)

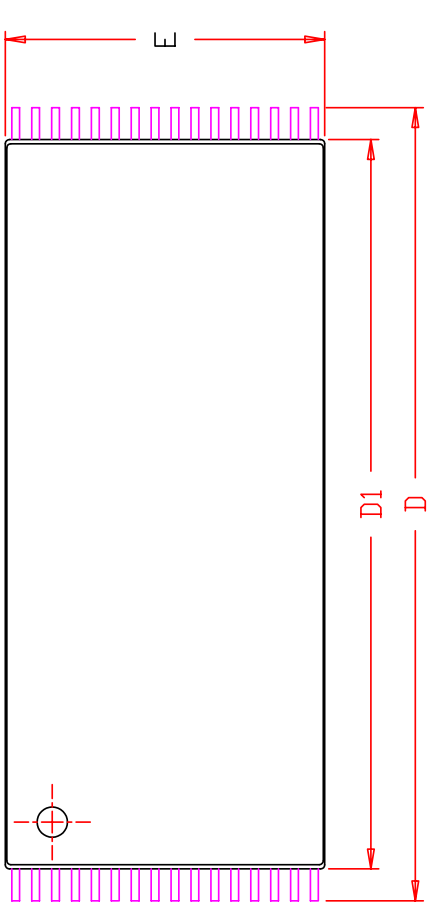
Industrial Range: –40°C to +85°C

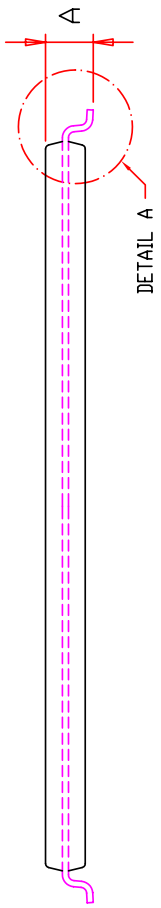
Speed (ns)	Order Part No.	Package
45	IS62WV5128DBLL-45TI	TSOP, TYPE I (8 x 20 mm)
45	IS62WV5128DBLL-45TLI	TSOP, TYPE I, Lead-free (8 x 20 mm)
45	IS62WV5128DBLL-45QLI	SOP, Lead-free
45	IS62WV5128DBLL-45T2I	TSOP, TYPE II
45	IS62WV5128DBLL-45T2LI	TSOP, TYPE II, Lead-free
45	IS62WV5128DBLL-45HI	sTSOP, TYPE I (8 x 13.4 mm)
45	IS62WV5128DBLL-45HLI	sTSOP, TYPE I, Lead-free (8 x 13.4 mm)
45	IS62WV5128DBLL-45BI	mini BGA (6mmx8mm)
45	IS62WV5128DBLL-45BLI	mini BGA (6mmx8mm), Lead-free


SYMBOL
DIMENSION IN MM
MIN NOM MAX
DIMENSION IN INCH
MIN NOM MAX
A 0.95 — 1.20 0.037 — 0.047
A1 0.05 — 0.15 0.002 — 0.008
A2 0.90 — 1.05 0.035 — 0.041
b 0.16 — 0.27 0.006 — 0.011
D 13.10 13.40 13.70 0.516 0.528 0.539
D1 11.70 11.80 11.90 0.461 0.465 0.469
E 7.90 8.00 8.10 0.311 0.315 0.319
e 0.50 BSC. 0.020 BSC.
L 0.30 0.50 0.70 0.012 0.020 0.028
L1 0.25 BSC. 0.010 BSC.
ZD 0.25 REF. 0.010 REF.
Θ 0 3° 5° 0 3° 5°
NOTE :
1. CONTROLLING DIMENSION : MM
2. DIMENSION D1 AND E DO NOT INCLUDE MOLD PROTRUSION.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION/INTRUSION.
4. Reference Document : JEDEC MO-183
ISSI
TITLE
32L 8x13.4mm TSOP-1 Package Outline
REV.
E
DATE
04/24/2008
ZD
b
e
A2
A1
32
17
E
1
16
D1
D
DETAIL A
A
DETAIL A
Θ
L
GAUGE PLANE
SEATING PLANE
L1

SYMBOL	DIMENSION IN MM		
	MIN	NOM	MAX
A	1.00	—	1.20
A1	0.05	—	0.20
A2	0.95	1.00	1.05
b	0.17	—	0.27
D	19.80	20.00	20.20
D1	18.30	18.40	18.50
E	7.80	8.00	8.20
e		0.50 BSC.	
L	0.40	—	0.70
L1		0.25 BSC.	
ZD		0.25 REF.	
θ	0	5°	8°

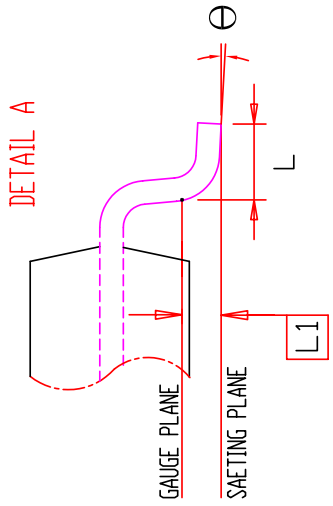




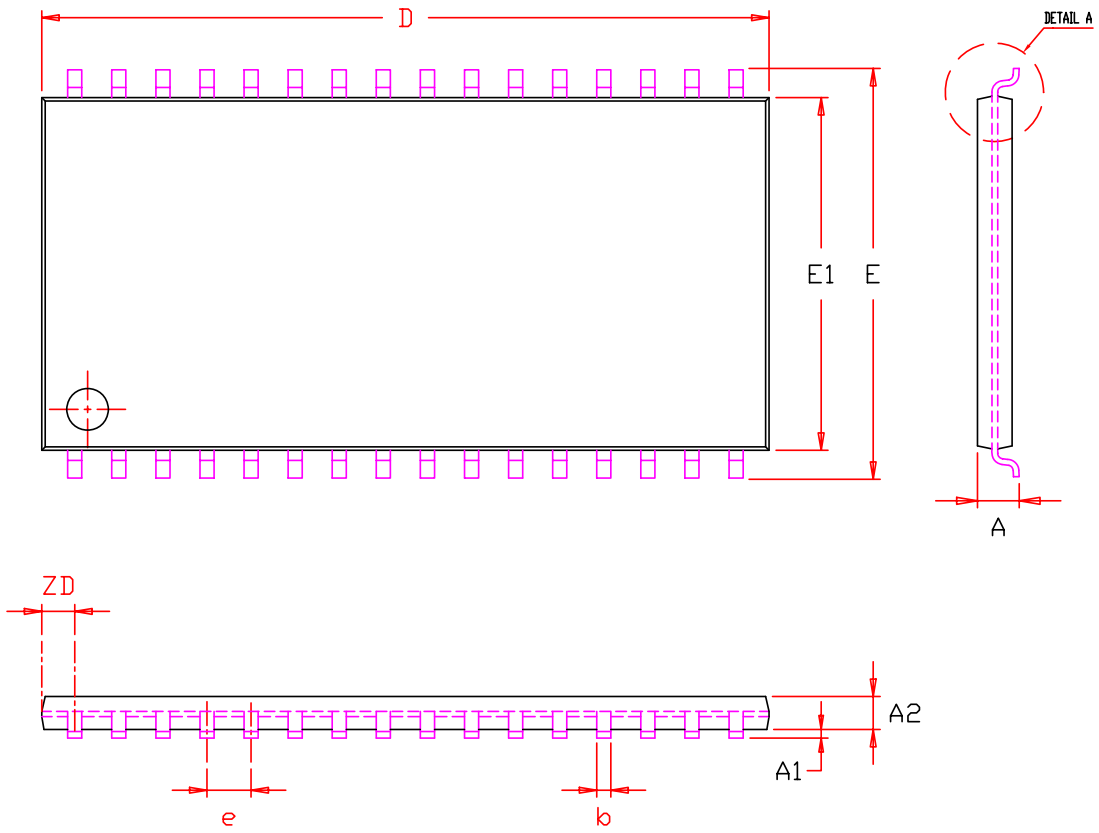


NOTE :

1. Controlling dimension : mm
2. Dimension D1 adn E do not include mold protrusion .
3. Dimension b does not include dambar protrusion/intrusion.
4. Formed leads shall be planar with respect to one another within 0.1mm at the seating plane after final test.



ISSI	TITLE	32L 8x20mm TSOP-1 Package Outline	REV.	E	DATE	06/08/2006



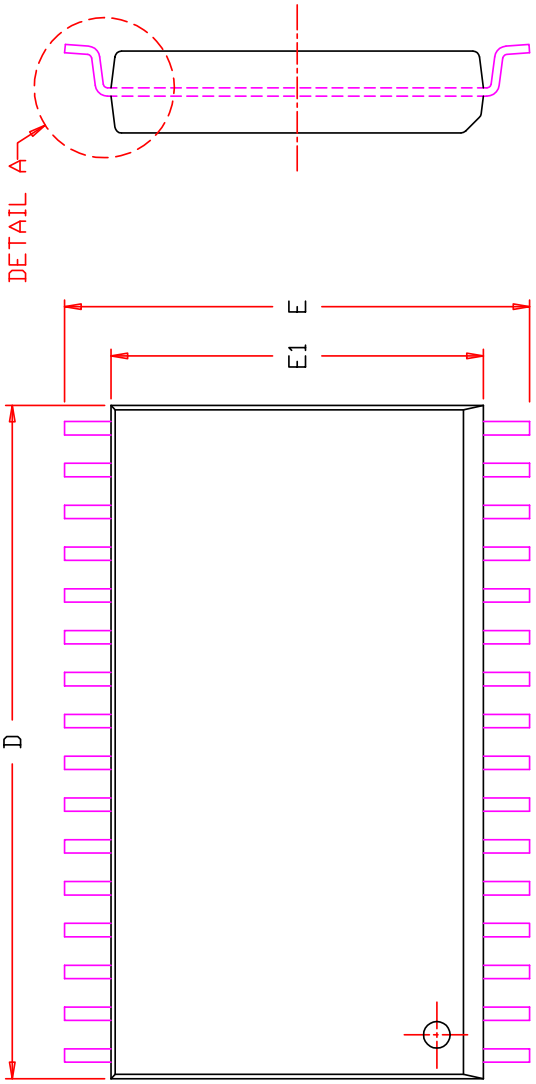
SYMBOL	DIMENSION IN MM			DIMENSION IN INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00		1.20	0.039		0.047
A1	0.05		0.15	0.002		0.006
A2	0.95	1.00	1.05	0.037	0.039	0.041
b	0.30		0.52	0.012		0.020
D	20.82	20.95	21.08	0.820	0.825	0.830
E	11.56	11.76	11.96	0.455	0.463	0.471
E1	10.03	10.16	10.29	0.395	0.400	0.405
e	1.27 BSC.			0.050 BSC.		
L	0.40	0.50	0.60	0.016	0.020	0.024
L1	0.25 BSC.			0.010 BSC.		
ZD	0.95 REF.			0.037 REF.		
θ	0		8°	0		8°

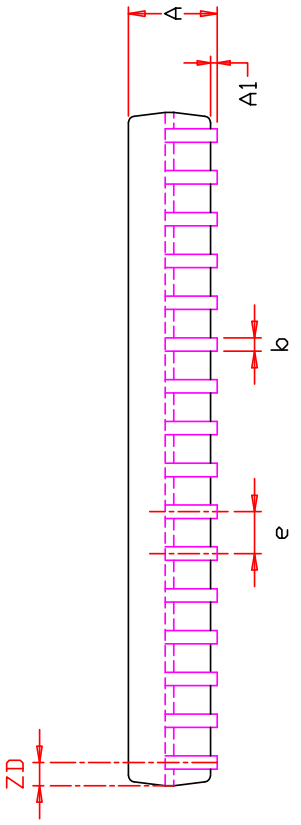
NOTE :

1. CONTROLLING DIMENSION : MM
2. DIMENSION D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION/INTRUSION.

ISSI	TITLE	32L 400mil TSOP-2 Package Outline	REV.	E	DATE	06/23/2009

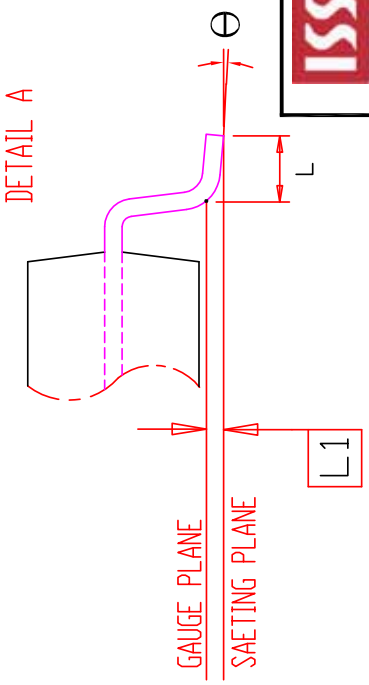
SYMBOL	DIMENSION IN MM			DIMENSION IN INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	2.62	—	3.12	0.103	—	0.123
A1	0.05	—	0.30	0.002	—	0.012
b	0.33	—	0.51	0.013	—	0.020
D	20.24	—	20.75	0.797	—	0.817
E	13.79	—	14.45	0.543	—	0.569
E1	11.18	—	11.43	0.440	—	0.450
e	1.27 BSC.			0.050 BSC.		
L	0.38	—	1.27	0.015	—	0.050
L1	0.25 BSC.			0.010 BSC.		
ZD	0.725 REF.			0.029 REF.		
θ	0	—	8°	0	—	8°



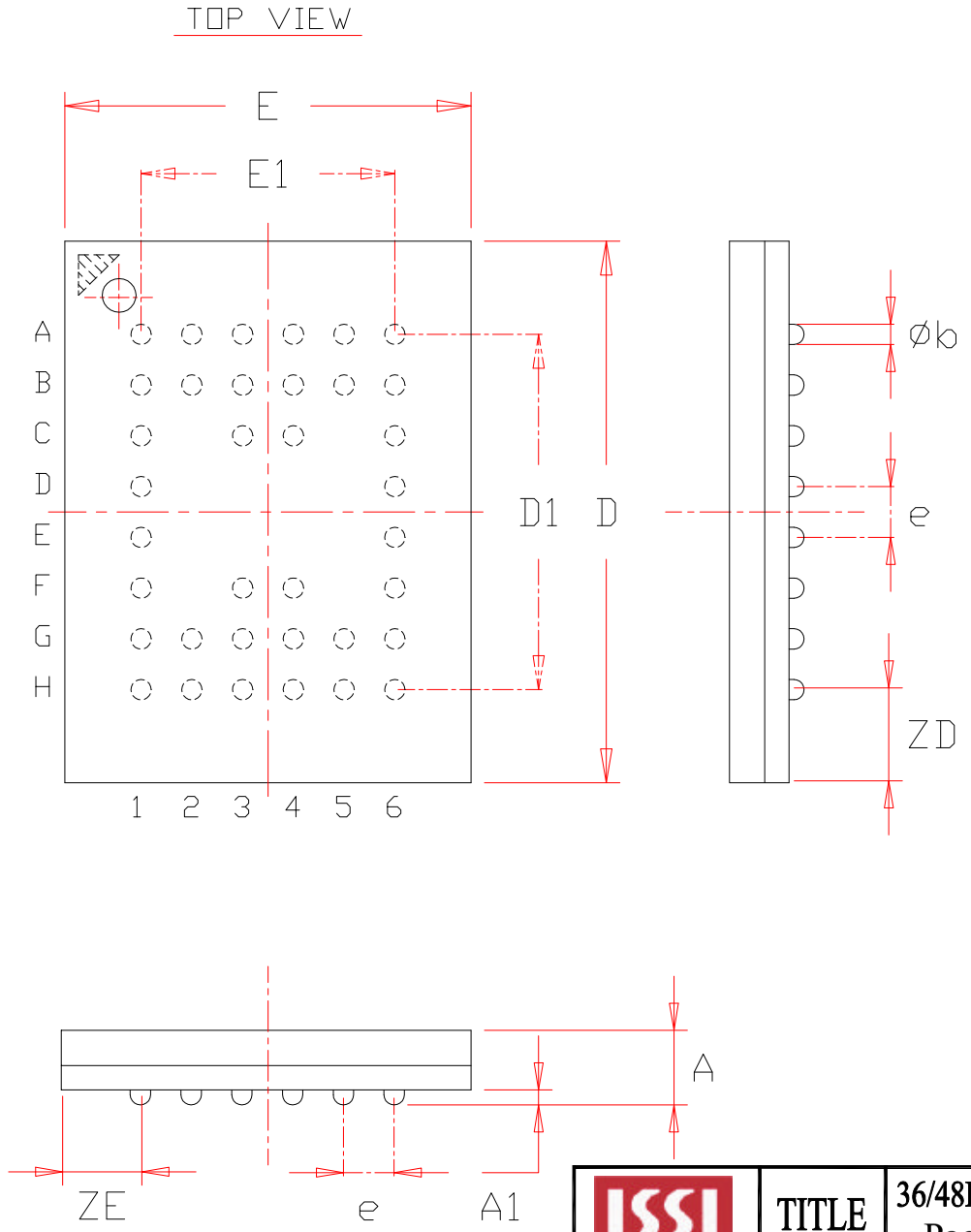


NOTE :

1. CONTROLLING DIMENSION : MM
2. DIMENSION D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION/INTRUSION.



ISSI	TITLE	32L 450mil SOP Package Outline	REV.	D	DATE	04/20/2009



SYMBOL	DIMENSION IN MM			DIMENSION IN INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A			1.20			0.047
A1	0.20		0.30	0.008		0.012
øb	0.30	0.35	0.40	0.012	0.014	0.016
D	7.90	8.00	8.10	0.311	0.315	0.319
D1	5.25 BSC.			0.207 BSC.		
E	5.90	6.00	6.10	0.232	0.236	0.240
E1	3.75 BSC.			0.148 BSC.		
e	0.75 BSC.			0.030 BSC.		
ZD	1.375 REF.			0.054 REF.		
ZE	1.125 REF.			0.044 REF.		

NOTE :

1. CONTROLLING DIMENSION : MM .
2. Reference document : JEDEC MO-207

ISSI	TITLE	36/48L 6x8mm TF-BGA Package Outline	REV.	E	DATE	08/12/2008

LifeElectronics
Живое партнерство

ООО «ЛайфЭлектроникс» **“LifeElectronics” LLC**

ИНН 7805602321 КПП 780501001 Р/С 40702810122510004610 ФАКБ "АБСОЛЮТ БАНК" (ЗАО) в г.Санкт-Петербурге К/С 30101810900000000703 БИК 044030703

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

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- *Специальные условия для постоянных клиентов.*
- *Подбор аналогов.*
- *Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.*

- *Приемлемые сроки поставки, возможна ускоренная поставка.*
- *Доставку товара в любую точку России и стран СНГ.*
- *Комплексную поставку.*
- *Работу по проектам и поставку образцов.*
- *Формирование склада под заказчика.*

- *Сертификаты соответствия на поставляемую продукцию (по желанию клиента).*
- *Тестирование поставляемой продукции.*
- *Поставку компонентов, требующих военную и космическую приемку.*
- *Входной контроль качества.*
- *Наличие сертификата ISO.*

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- *Регистрацию проекта у производителя компонентов.*
- *Техническую поддержку проекта.*
- *Защиту от снятия компонента с производства.*
- *Оценку стоимости проекта по компонентам.*
- *Изготовление тестовой платы монтаж и пусконаладочные работы.*

Тел: +7 (812) 336 43 04 (многоканальный)
Email: org@lifeelectronics.ru

www.lifeelectronics.ru